

PATENT  
790001-2037AMENDMENTS TO THE CLAIMS

Please amend the claims without prejudice, without admission, without surrender of subject matter, and without any intention of creating any estoppel as to equivalents, as follows.

In the Claims:

## Claim 1 (currently amended)

1. A semiconductor device comprising:
  - a semiconductor substrate;
  - a flat-plate-shaped cavity made in the semiconductor substrate; and
  - an element isolating region formed in the surface of the semiconductor substrate and located at the sides of the cavity, the cavity being wider than an element region provided on the cavity;  
wherein the element isolating region is less deep than the cavity and deeper than the element region.

## Claim 2 (cancelled)

## Claim 3 (previously presented)

3. The semiconductor device according to claim 1, wherein the element isolating region and the cavity enclose the element region and electrically separate the element region from the semiconductor substrate.

## Claim 4 (previously presented)

4. The semiconductor device according to claim 1, wherein only one element region is provided on the cavity.

## Claim 5 (cancelled)

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6. The semiconductor device according to claim 1, wherein the element isolating region is formed of an oxide film obtained by oxidizing the semiconductor substrate.

**Claim 7 (currently amended)**

7. A semiconductor device comprising:
  - a semiconductor substrate;
  - a plurality of flat-plate-shaped cavities made in the semiconductor substrate; and
  - an element isolating region formed in the surface of the semiconductor substrate between adjacent ones of the cavities, a part of the element isolating region being exposed to the cavities, each cavity being wider than each element region provided on each cavity, respectively,

wherein the element isolating region is less deep than the cavities and deeper than the element region.

**Claim 8 (cancelled)****Claim 9 (previously presented)**

9. The semiconductor device according to claim 7, wherein the element isolating region and the cavities enclose the element regions and electrically separate the element regions from the semiconductor substrate.

**Claim 10 (previously presented)**

10. The semiconductor device according to claim 7, wherein only one element region is provided on the cavity.

**Claim 11 (cancelled)**

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Claim 12 (original)

12. The semiconductor device according to claim 7, wherein the element isolating region is formed of an oxide film obtained by oxidizing the semiconductor substrate.

Claims 13-19 (cancelled)

Claim 20 (currently amended)

20. A method of fabricating a semiconductor device, comprising:  
making flat-plate-shaped cavities partly in a semiconductor substrate;  
forming an insulating film in the surface of the semiconductor substrate between adjacent ones of the cavities in such a manner that a part of the insulating film is exposed to the cavities so as to electrically separate element regions provided on the cavities from each other, each cavity being wider than each element region; and  
forming semiconductor elements on the element regions;  
wherein the insulating film is less deep than the cavities and deeper than the element region.

Claim 21 (original)

21. The method according to claim 20, wherein the insulating film is formed by oxidizing the surface of the semiconductor substrate.

Claim 22 (cancelled)

Claim 23 (original)

23. The method according to claim 20, wherein the insulating film and the cavities enclose the element regions and electrically separate the element regions from the semiconductor substrate.

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**Claim 24 (previously presented)**

24. The method according to claim 20, wherein only one element region provided on each of the cavities.

**Claims 25-26 (cancelled)**

**Claim 27. (previously presented)**

27. The semiconductor device according to claim 1, wherein the cavity has no element therein.

**Claim 28. (previously presented)**

28. The semiconductor device according to claim 7, wherein the cavity has no element therein.

**Claim 29. (previously presented)**

29. The semiconductor device according to claim 1, wherein the cavity has no element therein.